

#### STTH806DTI

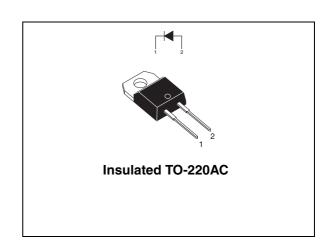
## Tandem 600 V hyperfast boost diode

Table 1. Main product characteristics

I <sub>F(AV)</sub>	8 A
V <sub>RRM</sub>	600 V
T <sub>j (max)</sub>	150° C
V <sub>F (max)</sub>	2.24 V
I <sub>RM (typ.)</sub>	4 A
t <sub>rr (typ.)</sub>	13 ns

#### Features and benefits

- Especially suited as boost diode in continuous mode power factor correctors and hard switching conditions
- Designed for high di/dt operation. Hyperfast recovery current to compete with SiC devices. Allows downsizing of mosfet and heatsinks
- Internal ceramic insulated devices with equal thermal conditions for both 300 V diodes
- Insulation (2500 V<sub>RMS</sub>) allows placement on same heatsink as mosfet and flexible heatsinking on common or separate heatsink
- Static and dynamic equilibrium of internal diodes are warranted by design
- Package Capacitance: C = 7 pF



#### **Description**

The TURBOSWITCH "H" is an ultra high performance diode composed of two 300 V dice in series. TURBOSWITCH "H" family drastically cuts losses in the associated MOSFET when run at high dl<sub>F</sub>/dt.

Table 2. Order codes

Part number	Marking
STTH806DTI	STTH806DTI

Table 3. Absolute ratings (limiting values)

Symbol	Parameter	Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	600	V
I <sub>F(RMS)</sub>	RMS forward voltage	14	Α
I <sub>FSM</sub>	Surge non repetitive forward current	180	Α
T <sub>stg</sub>	Storage temperature range	-65 to + 150	° C
Tj	Maximum operating junction temperature	150	° C

Characteristics STTH806DTI

## 1 Characteristics

Table 4. Thermal parameter

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case thermal resistance	2.6	°C/W

Table 5. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I <sub>B</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25° C	V V			10	μA
'R`	neverse leakage current	T <sub>j</sub> = 125° C	$V_R = V_{RRM}$		15	100	μΑ
V <sub>E</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25° C	I <sub>F</sub> = 8 A			3.6	V
VF ` /	Polward voltage drop	T <sub>j</sub> = 150° C	IF = 0 A		1.95	2.4	\ \ \

- 1. Pulse test: tp = 100 ms,  $\delta$  < 2%
- 2. Pulse test: tp = 380  $\mu$ s,  $\delta$  < 2%

To evaluate the conduction losses use the following equation:

 $P = 1.7 \text{ x } I_{F(AV)} + 0.087 I_{F}^{2}_{(RMS)}$ 

Table 6. Dynamic characteristics

Symbol	Parameter	Test conditions			Тур	Max	Unit
			$I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}, I_R = 1 \text{ A}$		13		
t <sub>rr</sub>	Reverse recovery time	T <sub>j</sub> = 25° C	$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$			30	ns
I <sub>RM</sub>	Reverse recovery current				4	5.5	
S	Reverse recovery softness factor	T <sub>j</sub> = 125° C	I <sub>F</sub> = 8 A, V <sub>R</sub> = 400,   VdI⊏/dt = - 200 A/us		0.4		Α
Q <sub>rr</sub>	Reverse recovery charges		1 d. F, d. 200 / 4 po		50		

Table 7. Turn-on switching characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
t <sub>fr</sub>	Forward recovery time	T <sub>j</sub> = 25° C	$I_F = 8 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_F \text{ max}$			200	ns
$V_{FP}$	Forward recovery voltage	T <sub>j</sub> = 25° C	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$			7	V

STTH806DTI Characteristics

Figure 1. Conduction losses versus average Figure 2. Forward voltage drop versus current forward current

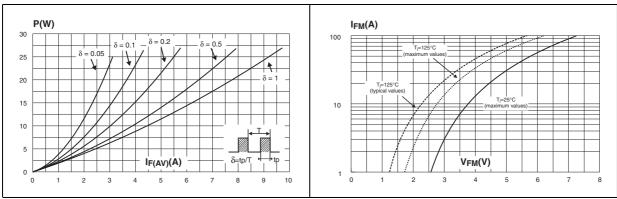


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl<sub>F</sub>/dt (typical values)

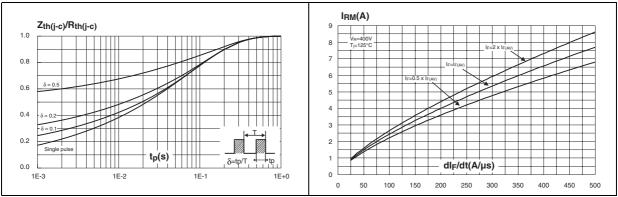
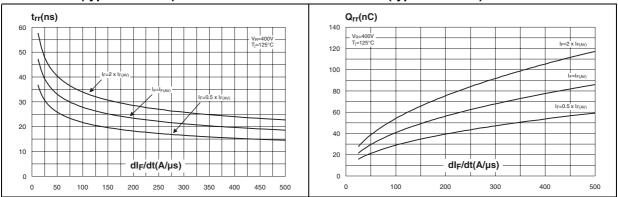


Figure 5. Reverse recovery time versus dI<sub>F</sub>/dt Figure 6. Reverse charges versus dI<sub>F</sub>/dt (typical values)

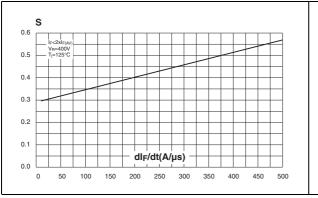


577

Characteristics STTH806DTI

Figure 7. Softness factor versus  $dI_F/dt$  (typical values)

Figure 8. Relative variation of dynamic parameters versus junction temperature (reference:  $T_i = 125^{\circ}$  C)



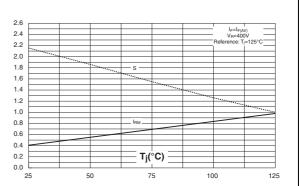
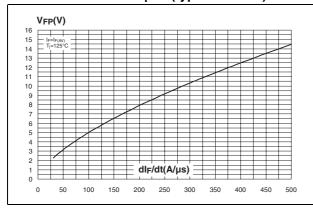
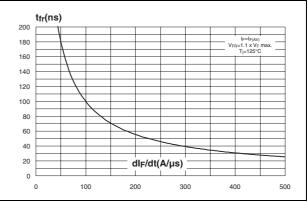


Figure 9. Transient peak forward voltage versus dl<sub>F</sub>/dt (typical values)

Figure 10. Forward recovery time versus  $dI_F/dt$  (typical values)





STTH806DTI Package information

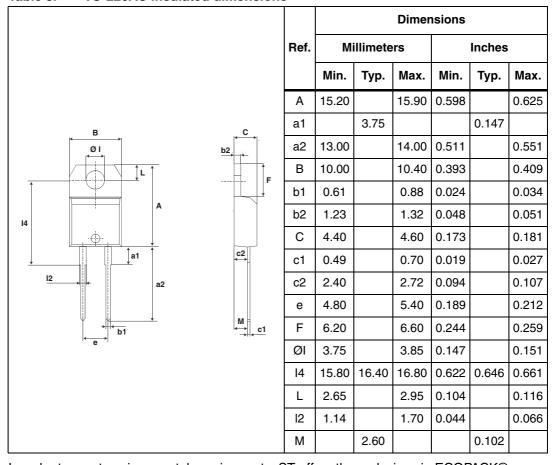
## 2 Package information

Epoxy meets UL94, V0

Cooling method: C

Recommended torque value: 0.4 to 0.6 Nm

Table 8. TO-220AC insulated dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

5/

Ordering information STTH806DTI

# **3** Ordering information

 Table 9.
 Ordering information

Part number	Marking	Package	Weight	Base qty	Delivery mode
STTH806DTI	STTH806DTI	TO-220AC	2.3 g	50	Tube

## 4 Revision history

Table 10. Revision history

Date	Revision	Changes
Oct-2003	2A	Initial release
May-2004	3	Reformatted
1 29111n-2005 1 4 1		Corrections to typographical errors. No technical changes.
		Reformatted to current standards. Removed I <sub>PEAK</sub> parameter from <i>Table 3: Absolute ratings (limiting values)</i> .

#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

